

1000um InGaAs PIN Module

Features

Active diameter 1000um
Small dark current
High reliability
Package can be customized

Applications

Fiber optics telecommunication networks
Digital receivers
Optical interconnects
Test and measurement
Datacom



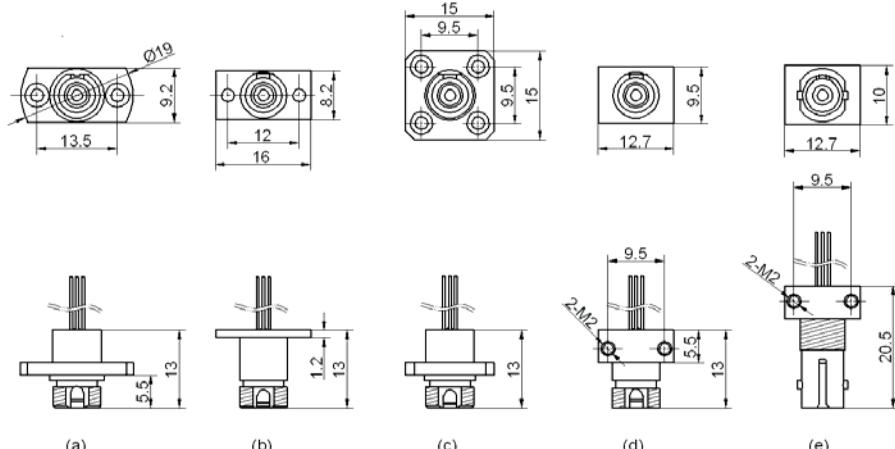
Absolute maximum ratings

| Parameter | Symbol | Value | Unit |
|----------------------------|----------------|---------|------|
| Storage temperature | Tst | -40~+85 | °C |
| Operating temperature | Top | -40~+85 | °C |
| Reverse voltage | V _R | 30 | V |
| Soldering temperature/time | — | 260/10 | °C/s |

Optical & electrical characteristics(T=25°C)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Test condition |
|--------------------|----------------|------|------|------|------|-------------------------------|
| Detection range | λ | 1100 | - | 1650 | nm | - |
| Dark current | I _d | - | 0.1 | 1 | nA | V _R =5V |
| Quantum efficiency | R | 0.80 | 0.85 | - | A/W | V _R =5V, λ=1310 nm |
| Capacitance | C _t | - | - | 0.75 | pF | V _R =5V |

Dimensions Diagram



PIN assignment

| pin | Function |
|---------|----------|
| 1(case) | GND |
| 2 | N |
| 3 | P |

Order information

| D | 1 | 10 | X | B |
|---|---|----|---------------|---------|
| | | | Range | Package |
| | | | 0,-70~+6dBm | 1,a |
| | | | 1, -60~+10dBm | 2,b |
| | | | 2, -50~+20dBm | 3,c |
| | | | | 4,d |
| | | | | 5,e |
| | | | | S,S |

This device is susceptible to damage as a result of electrostatic discharge (ESD). A static free environment is highly recommended. Follow guidelines according to proper ESD procedures

